

## SK26 SCHOTTKY RECTIFIER

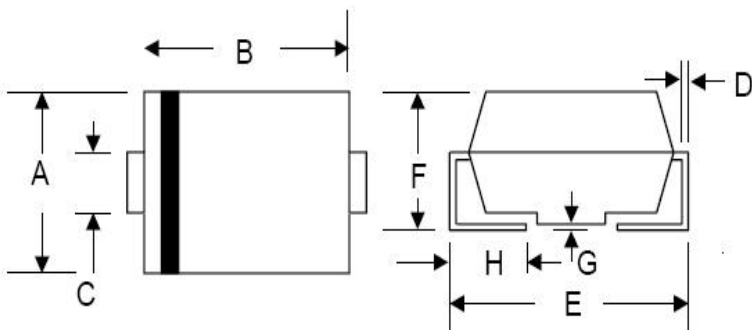
### Features:

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94F-0
- Green products in compliance the ROHS directive
- This is a Pb – Free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Mechanical Data:

- Case: Low Profile Molded plastic
- Terminals: Plated leads solderable per MIL-STD-750, Method 2026 guaranteed
- Polarity: Color band or cathode Notch
- Mounting Position: Any

### Mechanical Dimensions: In mm / Inches



SMB/DO-214AA				
Dim	Min	Max	Min	Max
A	3.30	3.94	0.130	0.155
B	4.06	4.70	0.160	0.185
C	1.91	2.11	0.075	0.083
D	0.152	0.305	0.006	0.012
E	5.08	5.59	0.2	0.220
F	2.13	2.44	0.084	0.096
G	0.051	0.203	0.002	0.008
H	0.76	1.27	0.029	0.05
		in mm		In inch

### SMB

**Marking Diagram:**


First row: Part Number

Second row: YYWWL

YY is the manufacture year, WW is the manufacture week code, L is the wafer's Lot Number

**Ordering Information:**

Device	Package	Shipping
SK26	SMB	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	$V_{RRM}$	-	60	V
Working Peak Reverse Voltage	$V_{RWM}$			
DC Blocking Voltage	$V_R$			
Maximum RMS voltage	$V_{RMS}$		42	V
Average Rectified Output Current	$I_O$	50% duty cycle @ $T_A = 55^\circ\text{C}$ , rectangular wave form	2.0	A
Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3 ms, half Sine pulse	50	A

**Electrical Characteristics:**

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	$V_F$	@ 2 A, Pulse $T_J = 25\text{ }^\circ\text{C}$	0.58	0.70	V
Reverse Current	$I_{R1}$	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^\circ\text{C}$	0.01	0.5	mA
	$I_{R2}$	@ $V_R = \text{rated } V_R$ $T_J = 100\text{ }^\circ\text{C}$	1	20	mA
Junction Capacitance	$C_T$	@ $V_R = 5\text{V}$ , $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	80	400	pF

\* Pulse Width < 300 $\mu$ s, Duty Cycle <2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-	-55 to +150	$^\circ\text{C}$
Typical Thermal Resistance Junction to Ambient (Note 1)	$R_{\theta JA}$	DC operation	75	K/W

Note: 1. mounted on P.C. Board with 8.0mm<sup>2</sup> copper pad areas.

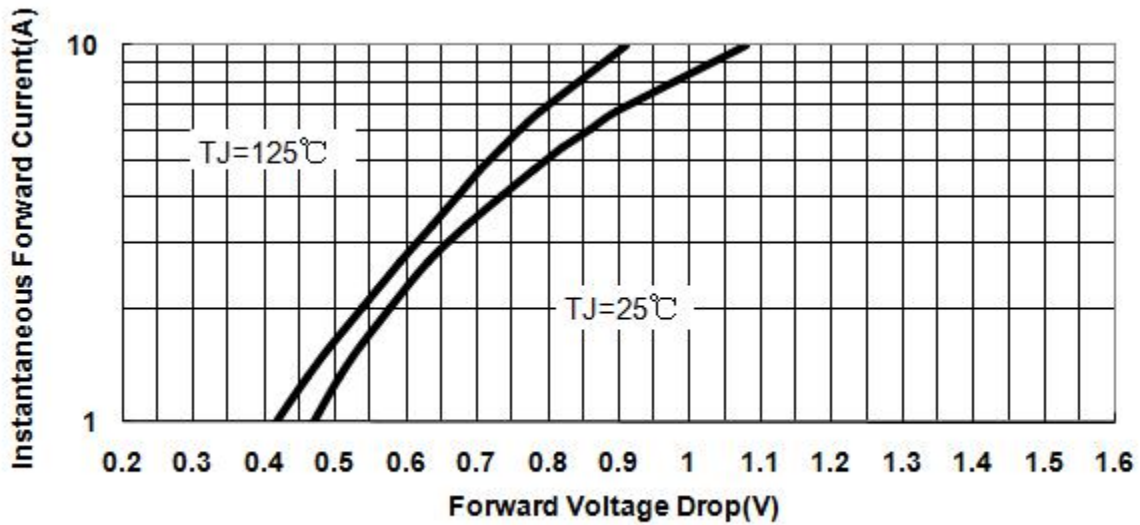


Fig.1-Typical Forward Voltage Drop Characteristics

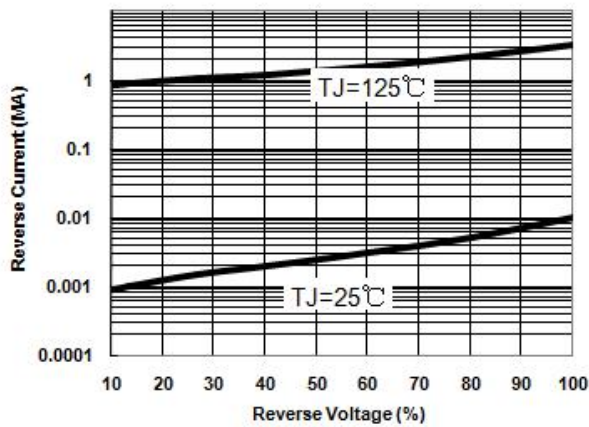


Fig.2-Typical Values Of Reverse Current VS.Reverse Voltage

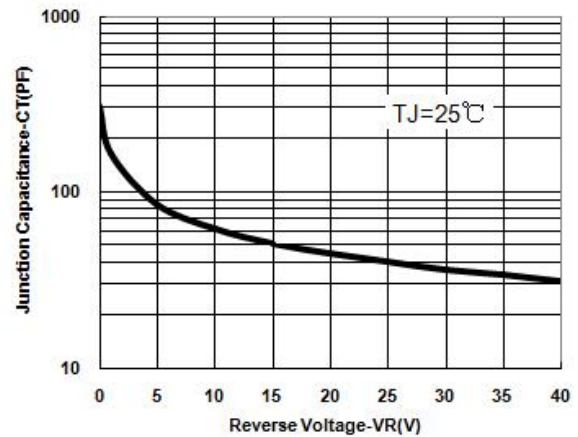


Fig.3-Typical Junction Capacitance Vs.Reverse Voltage

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